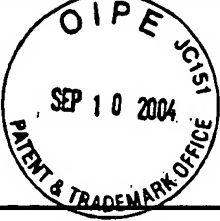


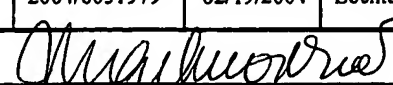


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U.S. PATENT DOCUMENTS							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	A1	2001/0003364	Sugawara <i>et al.</i>				
	A2	2002/0024395	Akatsuka <i>et al.</i>				
	A3	2002/0043660	Yamazaki <i>et al.</i>				
	A4	2002/0084000	Fitzgerald				
	A5	2002/0096717	Chu <i>et al.</i>				
	A6	2002/0100942	Fitzgerald <i>et al.</i>				
	A7	2002/0123167	Fitzgerald				
	A8	2002/0123183	Fitzgerald				
	A9	2002/0125471	Fitzgerald <i>et al.</i>				
	A10	2002/0168864	Cheng <i>et al.</i>				
	A11	2003/0003679	Doyle <i>et al.</i>				
	A12	2003/0013323	Hammond <i>et al.</i>				
	A13	2003/0034529	Fitzgerald <i>et al.</i>				
	A14	2003/0057439	Fitzgerald				
	A15	2003/0102498	Braithwaite <i>et al.</i>				
	A16	2003/0199126	Chu <i>et al.</i>				
	A17	2003/0203600	Chu <i>et al.</i>				
	A18	2003/0215990	Fitzgerald <i>et al.</i>				
	A19	2003/0218189	Christiansen				
	A20	2003/0227057	Lochtefeld <i>et al.</i>				
	A21	2004/0005740	Lochtefeld <i>et al.</i>				
	A22	2004/0014304	Bhattacharyya				
		A23	2004/0031979	Lochtefeld			06/06/2003
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U.S. PATENT DOCUMENTS							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
426	A24	2004/0041210	Mouli			09/02/2003	
	A25	2004/0075149	Fitzgerald <i>et al.</i>			07/23/2003	
	A26	4,010,045	Ruehrwein				
	A27	4,710,788	Dambkes <i>et al.</i>				
	A28	4,987,462	Kim <i>et al.</i>				
	A29	4,990,979	Otto				
	A30	4,997,776	Haramé <i>et al.</i>				
	A31	5,013,681	Godbey <i>et al.</i>				
	A32	5,155,571	Wang <i>et al.</i>				
	A33	5,166,084	Pfiester				
	A34	5,177,583	Endo <i>et al.</i>				
	A35	5,202,284	Kamins <i>et al.</i>				
	A36	5,207,864	Bhat <i>et al.</i>				
	A37	5,208,182	Narayan <i>et al.</i>				
	A38	5,212,110	Pfiester <i>et al.</i>				
	A39	5,221,413	Brasen <i>et al.</i>				
	A40	5,240,876	Gaul <i>et al.</i>				
	A41	5,241,197	Murakami <i>et al.</i>				
	A42	5,250,445	Bean <i>et al.</i>				
	A43	5,285,086	Fitzgerald				
	A44	5,291,439	Kauffmann <i>et al.</i>				
	A45	5,298,452	Meyerson				
✓	A46	5,310,451	Tejwani <i>et al.</i>				
EXAMINER <i>Murakami</i>				DATE CONSIDERED <i>09/22/04</i>			

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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
UH	A47	5,316,958	05/31/1994	Meyerson			
	A48	5,346,848	09/13/1994	Gruppen-Shemansky <i>et al.</i>			
	A49	5,374,564	12/20/1994	Bruehl			
	A50	5,399,522	03/21/1995	Ohuri			
	A51	5,413,679	05/09/1995	Godbey			
	A52	5,424,243	06/13/1995	Takasaki			
	A53	5,426,069	06/20/1995	Selvakumar <i>et al.</i>			
	A54	5,426,316	06/20/1995	Mohammad			
	A55	5,442,205	08/15/1995	Brasen <i>et al.</i>			
	A56	5,461,243	10/24/1995	Ek <i>et al.</i>			
	A57	5,461,250	10/24/1995	Burghartz <i>et al.</i>			
	A58	5,462,883	10/31/1995	Dennard <i>et al.</i>			
	A59	5,476,813	12/19/1995	Naruse			
	A60	5,479,033	12/26/1995	Baca <i>et al.</i>			
	A61	5,484,664	01/16/1996	Kitahara <i>et al.</i>			
	A62	5,523,243	06/04/1996	Mohammad			
	A63	5,523,592	06/04/1996	Nakagawa <i>et al.</i>			
	A64	5,534,713	07/09/1996	Ismail <i>et al.</i>			
	A65	5,536,361	07/16/1996	Kondo <i>et al.</i>			
	A66	5,540,785	07/30/1996	Dennard <i>et al.</i>			
	A67	5,572,043	11/05/1996	Shimizu <i>et al.</i>			
	A68	5,596,527	01/21/1997	Tomioka <i>et al.</i>			
✓	A69	5,617,351	04/01/1997	Bertin <i>et al.</i>			
EXAMINER <i>[Signature]</i>				DATE CONSIDERED 438 09/22/04			

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EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	A70	5,630,905	Lynch <i>et al.</i>				
	A71	5,659,187	Legoues <i>et al.</i>				
	A72	5,683,934	Candelaria				
	A73	5,698,869	Yoshimi <i>et al.</i>				
	A74	5,714,777	Ismail <i>et al.</i>				
	A75	5,728,623	Mori				
	A76	5,739,567	Wong				
	A77	5,759,898	Ek <i>et al.</i>				
	A78	5,777,347	Bartelink				
	A79	5,786,612	Otani <i>et al.</i>				
	A80	5,786,614	Chuang <i>et al.</i>				
	A81	5,792,679	Nakato				
	A82	5,808,344	Ismail <i>et al.</i>				
	A83	5,847,419	Imai <i>et al.</i>				
	A84	5,877,070	Goesele <i>et al.</i>				
	A85	5,891,769	Liaw <i>et al.</i>				
	A86	5,906,708	Robinson <i>et al.</i>				
	A87	5,906,951	Chu <i>et al.</i>				
	A88	5,912,479	Mori <i>et al.</i>				
	A89	5,943,560	Chang <i>et al.</i>				
A90	5,963,817	Chu <i>et al.</i>					
A91	5,966,622	Levine <i>et al.</i>					
A92	5,998,807	12/07/1999	Lustig <i>et al.</i>				
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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>At</i>	A93	6,013,134	01/11/2000	Chu <i>et al.</i>			
	A94	6,030,887	02/29/2000	Desai <i>et al.</i>			
	A95	6,030,889	02/29/2000	Aulicino <i>et al.</i>			
	A96	6,033,974	03/07/2000	Henley <i>et al.</i>			
	A97	6,033,995	03/07/2000	Muller			
	A98	6,058,044	05/02/2000	Sugiura <i>et al.</i>			
	A99	6,059,895	05/09/2000	Chu <i>et al.</i>			
	A100	6,074,919	06/13/2000	Gardner <i>et al.</i>			
	A101	6,096,590	08/01/2000	Chan <i>et al.</i>			
	A102	6,103,559	08/15/2000	Gardner <i>et al.</i>			
	A103	6,107,653	08/22/2000	Fitzgerald			
	A104	6,111,267	08/29/2000	Fischer <i>et al.</i>			
	A105	6,117,750	09/12/2000	Bensahel <i>et al.</i>			
	A106	6,130,453	10/10/2000	Mei <i>et al.</i>			
	A107	6,133,799	10/17/2000	Favors <i>et al.</i>			
	A108	6,140,687	10/31/2000	Shimomura <i>et al.</i>			
	A109	6,143,636	11/07/2000	Forbes <i>et al.</i>			
	A110	6,153,495	11/28/2000	Kub <i>et al.</i>			
	A111	6,154,475	11/28/2000	Soref <i>et al.</i>			
	A112	6,160,303	12/12/2000	Fattaruso			
	A113	6,162,688	12/19/2000	Gardner <i>et al.</i>			
	A114	6,184,111	02/06/2001	Henley <i>et al.</i>			
✓	A115	6,191,007	02/20/2001	Matsui <i>et al.</i>			
EXAMINER <i>Mei Johnson</i>				DATE CONSIDERED <i>09/22/04</i>			

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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
mt	A116	6,191,432	02/20/2001	Sugiyama <i>et al.</i>			
	A117	6,194,722	02/27/2001	Fiorini <i>et al.</i>			
	A118	6,204,529	03/20/2001	Lung <i>et al.</i>			
	A119	6,207,977	03/27/2001	Augusto			
	A120	6,210,988	04/03/2001	Howe <i>et al.</i>			
	A121	6,218,677	04/17/2001	Broekaert			
	A122	6,232,138	05/15/2001	Fitzgerald <i>et al.</i>			
	A123	6,235,567	05/22/2001	Huang			
	A124	6,242,324	06/05/2001	Kub <i>et al.</i>			
	A125	6,249,022	06/19/2001	Lin <i>et al.</i>			
	A126	6,251,755	06/26/2001	Furukawa <i>et al.</i>			
	A127	6,261,929	07/17/2001	Gehrke <i>et al.</i>			
	A128	6,266,278	07/24/2001	Harari <i>et al.</i>			
	A129	6,271,551	08/07/2001	Schmitz <i>et al.</i>			
	A130	6,271,726	08/07/2001	Fransis <i>et al.</i>			
	A131	6,291,321	09/18/2001	Fitzgerald			
	A132	6,313,016	11/06/2001	Kibbel <i>et al.</i>			
	A133	6,316,301	11/13/2001	Kant			
	A134	6,323,108	11/27/2001	Kub <i>et al.</i>			
	A135	6,329,063	12/11/2001	Lo <i>et al.</i>			
	A136	6,335,546	01/01/2002	Tsuda <i>et al.</i>			
	A137	6,339,232	01/15/2002	Takagi			
✓	A138	6,350,993	02/26/2002	Chu <i>et al.</i>			
EXAMINER <i>M. Tran</i>				DATE CONSIDERED <i>09/22/04</i>			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
UH	A139	6,352,909	03/05/2002	Usenko			
	A140	6,368,733	04/09/2002	Nishinaga			
	A141	6,372,356	04/16/2002	Thornton <i>et al.</i>			
	A142	6,372,593	04/16/2002	Hattori <i>et al.</i>			
	A143	6,399,970	06/04/2002	Kubo <i>et al.</i>			
	A144	6,403,975	06/11/2002	Brunner <i>et al.</i>			
	A145	6,407,406	06/18/2002	Tezuka			
	A146	6,420,937	07/16/2002	Akatsuka <i>et al.</i>			
	A147	6,425,951	07/30/2002	Chu <i>et al.</i>			
	A148	6,429,061	08/06/2002	Rim			
	A149	6,521,041	02/18/2003	Wu <i>et al.</i>			
	A150	6,524,935	02/25/2003	Canaperi <i>et al.</i>			
	A151	6,555,839	04/29/2003	Fitzgerald			
	A152	6,573,126	06/03/2003	Cheng <i>et al.</i>			
	A153	6,583,015	06/24/2003	Fitzgerald <i>et al.</i>			
	A154	6,593,191	07/15/2003	Fitzgerald			
	A155	6,593,641	07/15/2003	Fitzgerald			
	A156	6,602,613	08/05/2003	Fitzgerald			
	A157	6,603,156	08/05/2003	Rim			
	A158	6,646,322	11/11/2003	Fitzgerald			
	A159	6,649,480	11/18/2003	Fitzgerald <i>et al.</i>			
	A160	6,677,192	01/13/2004	Fitzgerald			
✓	A161	6,703,144	03/09/2004	Fitzgerald			03/18/2003
EXAMINER <i>Meashon</i>				DATE CONSIDERED <i>09/22/04</i>			

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MH	A162	6,703,688	03/09/2004	Fitzgerald			07/16/2001		
	A163	6,709,903	03/23/2004	Christiansen			04/30/2003		
	A164	6,713,326	03/30/2004	Cheng <i>et al.</i>			03/04/2003		
	A165	6,723,661	04/20/2004	Fitzgerald			07/16/2001		
	A166	6,724,008	04/20/2004	Fitzgerald			07/16/2001		
	A167	6,730,551	05/04/2004	Lee <i>et al.</i>			08/02/2002		
	A168	6,737,670	05/18/2004	Cheng <i>et al.</i>			03/07/2003		
	A169	6,750,130	06/15/2004	Fitzgerald			01/07/2001		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
MH	B1	41 01 167	07/23/1992	DE				N	Y (Abstract only)
	B2	0 514 018	11/19/1992	EP				N	Y
	B3	0 587 520	03/16/1994	EP				N	Y
	B4	0 683 522	11/22/1995	EP				N	Y
	B5	0 828 296	03/11/1998	EP				N	Y
	B6	0 829 908	03/18/1998	EP				N	Y
	B7	0 838 858	04/29/1998	EP				N	Y (Abstract only)
	B8	1 020 900	07/19/2000	EP				N	Y
	B9	1 174 928	01/23/2002	EP				N	Y
	B10	2 701 599	09/01/1993	FR				Y	Y
	B11	2 342 777	04/19/2000	GB				N	Y
	B12	61/141116	06/28/1986	JP				N	Y (Abstract only)
	B13	2/210816	08/22/1990	JP				N	Y (Abstract only)
EXAMINER <i>Chuan Lu</i>				DATE CONSIDERED <i>09/22/04</i>					

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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
11/1	B14	3/036717	02/18/1991	JP				N	Y
	B15	4-307974	10/30/1992	JP				N	Y (Abstract only)
	B16	5-166724	07/23/1993	JP				N	Y (Abstract only)
	B17	6-177046	06/24/1994	JP				N	Y (Abstract only)
	B18	6-244112	09/02/1994	JP				Y	Y
	B19	6-252046	09/09/1994	JP				Y	Y
	B20	7-094420	04/07/1995	JP				N	Y (Abstract only)
	B21	7-106446	04/21/1995	JP				Y	Y
	B22	7-240372	09/12/1995	JP				Y	Y
	B23	10-270685	10/09/1998	JP				N	Y
	B24	11-233744	08/27/1999	JP				N	Y (Abstract only)
	B25	2000-021783	01/21/2000	JP				N	Y
	B26	2000-031491	01/28/2000	JP				Y	Y
	B27	2001-319935	11/16/2001	JP				N	Y
	B28	2002-076334	03/15/2002	JP				N	Y
	B29	2002-164520	06/07/2002	JP				N	Y
	B30	2002-289533	10/04/2002	JP				N	Y
	B31	98/59365	12/30/1998	WO				N	Y
	B32	99/53539	10/21/1999	WO				N	Y
	B33	00/48239	08/17/2000	WO				N	Y
EXAMINER <i>M. Huong C. Tran</i>				DATE CONSIDERED <i>09/22/04</i>					

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UH	B34	00/54338	09/14/2000	WO				N	Y	
	B35	01/22482	03/29/2001	WO				N	Y	
	B36	01/54202	07/26/2001	WO				N	Y	
	B37	01/93338	12/06/2001	WO				N	Y	
	B38	01/99169	12/27/2001	WO				N	Y	
	B39	02/13262	02/14/2002	WO				N	Y	
	B40	02/15244	02/21/2002	WO				N	Y	
	B41	02/27783	04/04/2002	WO				N	Y	
	B42	02/47168	06/13/2002	WO				N	Y	
	B43	02/071488	09/12/2002	WO				N	Y	
	B44	02/071491	09/12/2002	WO				N	Y	
	B45	02/071495	09/12/2002	WO				N	Y	
	B46	02/082514	10/17/2002	WO				N	Y	
	B47	04/006311	01/15/2004	WO				N	Y	
	B48	04/006327	01/15/2004	WO				N	Y	
OTHER ART, JOURNAL ARTICLES, ETC.										
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)									
UH	C1	Armstrong <i>et al.</i> , "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," IEDM Technical Digest (1995 International Electron Devices Meeting), pp. 761-764.								
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OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
ut	C2	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices," Ph.D. Thesis, Massachusetts Institute of Technology, Department of Electrical Engineering and Computer Science (June 30, 1999), pp. 1-154.							
	C3	Augusto <i>et al.</i> , "Proposal for a New Process Flow for the Fabrication of Silicon-based Complementary MOD-MOSFETs without Ion Implantation," <u>Thin Solid Films</u> , Vol. 294, No. 1-2 (February 15, 1997), pp. 254-258.							
	C4	Barradas <i>et al.</i> , "RBS analysis of MBE-grown SiGe/(001) Si heterostructures with thin, high Ge content SiGe channels for HMO transistors," <u>Modern Physics Letters B</u> , Vol. 15, No. 28-29 (December 2001), abstract.							
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

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
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